A M Kadykov

List of Publications by Year in descending order

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		759190	642715
39	529	12	23
papers	citations	h-index	g-index
47	47	47	304
all docs	docs citations	times ranked	citing authors

#	Article	IF	CITATIONS
1	Temperature-driven massless Kane fermions in HgCdTe crystals. Nature Communications, 2016, 7, 12576.	12.8	73
2	Stimulated emission from HgCdTe quantum well heterostructures at wavelengths up to 19.5 <i>μ</i> m. Applied Physics Letters, 2017, 111, .	3.3	58
3	HgCdTe-based heterostructures for terahertz photonics. APL Materials, 2017, 5, .	5.1	49
4	Temperature-Induced Topological Phase Transition in HgTe Quantum Wells. Physical Review Letters, 2018, 120, 086401.	7.8	43
5	Temperature-driven single-valley Dirac fermions in HgTe quantum wells. Physical Review B, 2017, 96, .	3.2	38
6	Long wavelength stimulated emission up to 9.5 <i>μ</i> m from HgCdTe quantum well heterostructures. Applied Physics Letters, 2016, 108, .	3.3	34
7	Time resolved photoluminescence spectroscopy of narrow gap Hg1â^'xCdxTe/CdyHg1â^'yTe quantum well heterostructures. Applied Physics Letters, 2014, 105, 022102.	3.3	28
8	Terahertz photoconductivity of double acceptors in narrow gap HgCdTe epitaxial films grown by molecular beam epitaxy on GaAs(013) and Si(013) substrates. Semiconductor Science and Technology, 2017, 32, 095007.	2.0	27
9	Stimulated emission in the 28–35 μm wavelength range from Peltier cooled HgTe/CdHgTe quantum well heterostructures. Optics Express, 2018, 26, 12755.	3.4	26
10	Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. Physical Review B, 2018, 97, .	3.2	24
11	Terahertz detection of magnetic field-driven topological phase transition in HgTe-based transistors. Applied Physics Letters, 2015, 107, .	3.3	13
12	Terahertz imaging of Landau levels in HgTe-based topological insulators. Applied Physics Letters, 2016, 108, .	3.3	13
13	Long wavelength superluminescence from narrow gap HgCdTe epilayer at 100 K. Applied Physics Letters, 2015, 107, .	3.3	11
14	Features of Photoluminescence of Double Acceptors in HgTe/CdHgTe Heterostructures with Quantum Wells in a Terahertz Range. JETP Letters, 2019, 109, 657-662.	1.4	10
15	Magnetospectroscopy of double HgTe/CdHgTe quantum wells. Semiconductors, 2016, 50, 1532-1538.	0.5	9
16	On the band spectrum in p-type HgTe/CdHgTe heterostructures and its transformation under temperature variation. Semiconductors, 2017, 51, 1531-1536.	0.5	8
17	Long-wavelength stimulated emission and carrier lifetimes in HgCdTe-based waveguide structures with quantum wells. Semiconductors, 2016, 50, 1651-1656.	0.5	7
18	Investigation of possibility of VLWIR lasing in HgCdTe based heterostructures. Journal of Physics: Conference Series, 2015, 647, 012008.	0.4	6

#	Article	IF	Citations
19	Impurity-induced photoconductivity of narrow-gap Cadmium–Mercury–Telluride structures. Semiconductors, 2015, 49, 1605-1610.	0.5	6
20	Mercury vacancies as divalent acceptors in Hg y Te1 $\hat{a}\in$ "y /Cd x Hg1 $\hat{a}\in$ " x Te structures with quantum wells. Semiconductors, 2016, 50, 1662-1668.	0.5	6
21	Investigation of HgCdTe waveguide structures with quantum wells for long-wavelength stimulated emission. Semiconductors, 2017, 51, 1557-1561.	0.5	6
22	Terahertz Photoluminescence of Double Acceptors in Bulky Epitaxial HgCdTe Layers and HgTe/CdHgTe Structures with Quantum Wells. Journal of Experimental and Theoretical Physics, 2018, 127, 1125-1129.	0.9	6
23	Effect of Features of the Band Spectrum on the Characteristics of Stimulated Emission in Narrow-Gap Heterostructures with HgCdTe Quantum Wells. Semiconductors, 2018, 52, 1375-1379.	0.5	6
24	Experimental Observation of Temperature-Driven Topological Phase Transition in HgTe/CdHgTe Quantum Wells. Condensed Matter, 2019, 4, 27.	1.8	5
25	Calculation of Multiply Charged States of Impurity-Defect Centers in Epitaxial Hg1 –xCdxTe Layers. Semiconductors, 2018, 52, 1369-1374.	0.5	4
26	Terahertz Spectroscopy of Two-Dimensional Semimetal in Three-Layer InAs/GaSb/InAs Quantum Well. JETP Letters, 2019, 109, 96-101.	1.4	4
27	Cyclotron resonance of dirac fermions in InAs/GaSb/InAs quantum wells. Semiconductors, 2017, 51, 38-42.	0.5	3
28	Many-particle effects in optical transitions from zero-mode Landau levels in HgTe quantum wells. Physical Review B, 2020, 102, .	3.2	3
29	Observation of topological phase transition by terahertz photoconductivity in HgTeâ€based transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 534-537.	0.8	2
30	Nonresonant radiative exciton transfer by near field between quantum wells. Journal of Experimental and Theoretical Physics, 2013, 117, 944-949.	0.9	1
31	Terahertz excitations in HgTe-based field effect transistors. Journal of Physics: Conference Series, 2015, 647, 012009.	0.4	0
32	Terahertz cyclotron emission from HgCdTe bulk films. , 2016, , .		0
33	THz magnetospectroscopy of double HgTe quantum well. , 2016, , .		0
34	Long-wavelength stimulated emission in HgCdTe quantum well waveguide heterostructures. , 2016, , .		0
35	THz lasers based on narrow-gap semiconductors. , 2016, , .		0
36	Spectroscopy of Temperature-Driven Single Valley Dirac Fermions in HgTe/CdHgTe Quantum Wells. , 2018, , .		0

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#	Article	IF	CITATIONS
37	HgCdTe based quantum well heterostructures for long-wavelength lasers operating in 5 - 15 THz range. Journal of Physics: Conference Series, 2018, 1092, 012126.	0.4	0
38	HgTe/CdTe Quantum Well Heterostructures For Far and Mid IR Lasers. , 2018, , .		0
39	Magnetooptical Studies and Stimulated Emission in Narrow Gap HgTe/CdHgTe Structures in the Very Long Wavelength Infrared Range. Semiconductors, 2018, 52, 436-441.	0.5	O